HSMS-282Y

RF Schottky Barrier Diodes In Surface Mount SOD-523 Package



Data Sheet

Description

The HSMS-282Y of Avago Technologies is a RF Schottky Barrier Diode, featuring low series resistance, low forward voltage at all current levels and good RF characteristics. The device is housed in a miniature low cost surface mount SOD-523 package. This miniature package is particularly useful in the application where board space is the major concern.ApplicationsThe HSMS-282Y is specially designed for both analog and digital applications. The typical applications are mixing, detecting, switching, sampling, clamping and wave shaping.

Table 1. Absolute Maximum Ratings [1] at $Tc = +25^{\circ}C$

Symbol	Parameter	Unit	Max Rating
I _F	Forward Current (1 µs Pulse)	Amp	1
P _{IV}	Peak Inverse Voltage	V	15
Tj	Junction Temperature	°C	150
T _{STG}	Storage Temperature	°C	-65 to 150
θјb	Thermal Resistance ^[2]	°C/W	175

Notes:

- 1. Operation in excess of any one of these conditions may result in permanent damage to the device.
- 2. Thermal Resistance is measured from junction to board using IR microscopy method.

Features

- Space saving SOD-523 package
- Low Turn-On Voltage
- Low Series Resistance
- Tape and Reel Options Available
- MSL 1 & Lead Free

Package Marking and Pin Connections



Note: Package marking provides orientation and identification

"Y" = Device Code

"?" = Month code indicates the month of manufacture

Table 2. Electrical Specifications at $Tc = +25^{\circ}C$

	Minimum Breakdown Voltage V _{BR} (V)	Maximum Forward Voltage V _F (mV)	Maximum Forward Voltage V _F (V)	Maximum Reverse Leakage I _R (nA)	Maximum Capacitance C _T (pF)	Typical Dynamic Resistance R _D (Ohm) ^[2]
	15	340	0.5	100	1.0	12
Test Conditions	$V_R = V_{BR}$ Measure $I_R \le 100 \mu A$	I _F = 1mA	$I_F = 10 \text{mA}$	V _{R} = 1V	$V_{\mathbf{R}} = 0$ Vf = 1 MHz	$I_F = 5 \text{mA}$

Notes:

- 1. Effective carrier lifetime(τ) for the diode is 100 ps maximum measured with Krakaver method at 5 mA
- 2. RD = Rs + 5.2 Ohm @ 25 °C and I_F = 5 mA

Typical Performance Curves at $Tc = +25^{\circ}C$

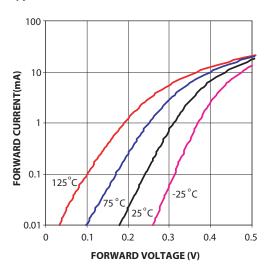


Figure 1. Forward Currect vs. Forward Voltage at temperature

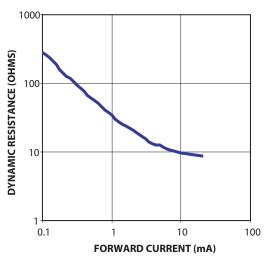


Figure 3. Dynamic Resistance vs. Forward Current

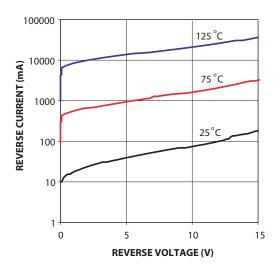


Figure 2. Reverse Current vs. Reverse Voltage at temperature

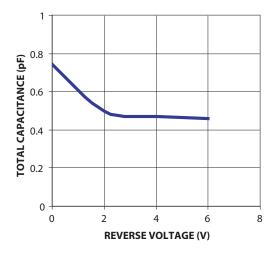


Figure 4. Total Capacitance vs. Reverse Bias at 1MHz

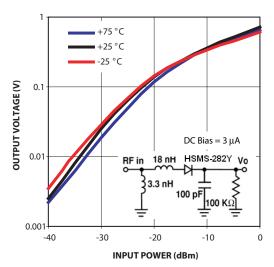


Figure 5. Typical Output Voltage vs. Input Power, Small Signal Detector Operating at 850 MHz.

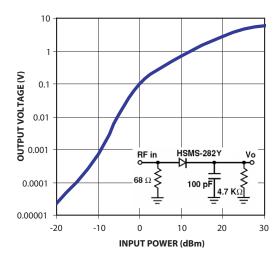
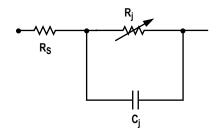


Figure 6. Typical Output Voltage vs. Input Power, Large Signal Detector Operating at 915 MHz.

Linear Equivalent Circuit Model Diode Chip



R_S = series resistance (see Table of SPICE parameters)

C_i = junction capacitance (see Table of SPICE parameters)

$$R_j = \frac{8.33 \times 10^{-5} \text{ nT}}{I_h + I_s}$$

where

I_b = externally applied bias current in amps

I_s = saturation current (see table of SPICE parameters)

T = temperature, K

n = ideality factor (see table of SPICE parameters)

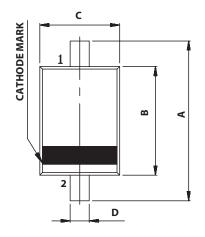
Note:

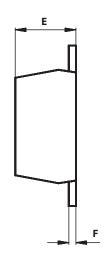
To effectively model the packaged HSMS-282x product, please refer to Application Note AN1124.

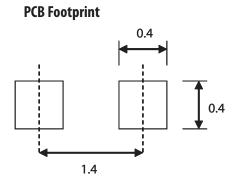
SPICE Parameters

Parameter	Units	HSMS-282Y
B _V	V	15
C_{J0}	pF	0.7
E _G	eV	0.69
I _{BV}	A	1E-4
Ις	Α	2.2E-8
N		1.08
R_{S}	Ω	6.0
P_B	V	0.65
P _T		2
М		0.5

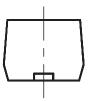
Package Outline and Dimension





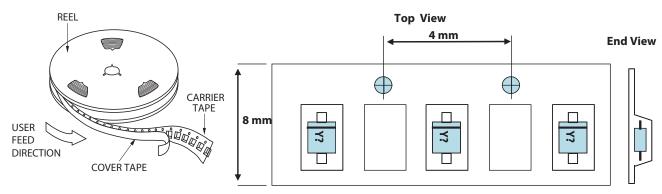


Unit:mm

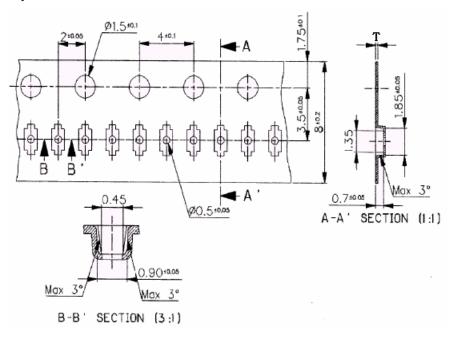


DIM	MILLIMETERS
Α	1.60 ± 0.10
В	1.20 ± 0.10
С	0.80 ± 0.10
D	0.30 ± 0.05
Е	0.60 ± 0.10
F	0.13 ± 0.05

Device Orientation



Tape Dimension



Specification < Unit : mm >

hole pitch : 50 Pitch Tolerance : 200 ± 0.3

General Tolerance: ± 0.1

Surface resistance: 104 ~ 108 W/cm3

Part Number Ordering Information

Part number	No. of Units	Container
HSMS-282Y-BLKG	100	Anti-static bag
HSMS-282Y-TR1G	3000	7" reel

For product information and a complete list of distributors, please go to our web site:

www.avagotech.com

